Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max $T_A = 25°C$
20V	55mΩ @ V_{GS} = 4.5V	4.0A
	70mΩ @ V_{GS} = 2.5V	3.5A
	90mΩ @ V_{GS} = 1.8V	3.1A
	130mΩ @ V_{GS} = 1.5V	2.5A

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions

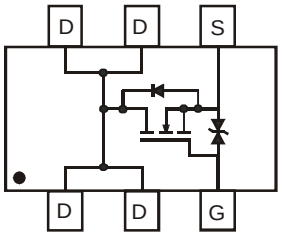
Mechanical Data

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.015 grams (approximate)

ESD PROTECTED

SOT26

Top View



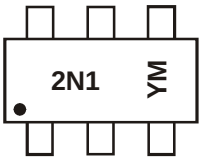
Top View
Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2100UDM-7	SOT26	3000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com..

Marking Information



2N1 = Marking Code
YM = Date Code Marking
Y = Year (ex: U = 2007)
M = Month (ex: 9 = September)

Date Code Key

Year	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	U	V	W	X	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	±8	V
Continuous Drain Current (Note 6) V_{GS} = 4.5V	Steady State	T_A = 25°C T_A = 70°C	I_D	4.0 3.1	A
	t<10s	T_A = 25°C T_A = 70°C	I_D	4.5 3.5	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I_{DM}	13	A
Maximum Body Diode Continuous Current			I_S	1.5	A

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T_A = 25°C	P_D	1	W
	T_A = 70°C		0.6	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	$R_{\theta JA}$	127	°C/W
	t<10s		91	
Total Power Dissipation (Note 6)	T_A = 25°C	P_D	1.5	W
	T_A = 70°C		0.9	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	$R_{\theta JA}$	85	°C/W
	t<10s		63	
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	3.1	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	20	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±1	µA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	0.6	—	1.0	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	—	32	55	mΩ	V_{GS} = 4.5V, I_D = 6A
		—	43	70		V_{GS} = 2.5V, I_D = 4.0A
		—	56	90		V_{GS} = 1.8V, I_D = 1.5A
		—	80	130		V_{GS} = 1.5V, I_D = 1.0A
Forward Transfer Admittance	$\|Y_{fs}\|$	—	8	—	S	V_{DS} =10V, I_D = 6A
Diode Forward Voltage	V_{SD}	—	0.7	1.1	V	V_{GS} = 0V, I_S = 2A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	555	—	pF	V_{DS} = 10V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	112	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	84	—	pF	
Total Gate Charge	Q_g	—	8.8	—	nC	V_{DS} = 10V, V_{GS} = 4.5V, I_D = 6.5A
Gate-Source Charge	Q_{gs}	—	1.4	—	nC	
Gate-Drain Charge	Q_{gd}	—	3	—	nC	
Turn-On Delay Time	$t_{D(on)}$	—	53	—	ns	V_{DS} = 10V, I_D = 1.0A V_{GS} = 4.5V, R_G = 6Ω
Turn-On Rise Time	t_r	—	78	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	561	—	ns	
Turn-Off Fall Time	t_f	—	234	—	ns	

Notes:
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate
7. Short duration pulse test used to minimize self-heating effect
8. Guaranteed by design. Not subject to production testing

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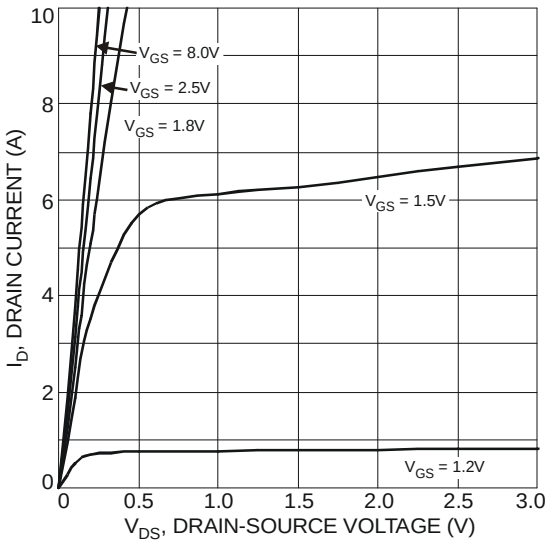

Fig. 1 Typical Output Characteristic

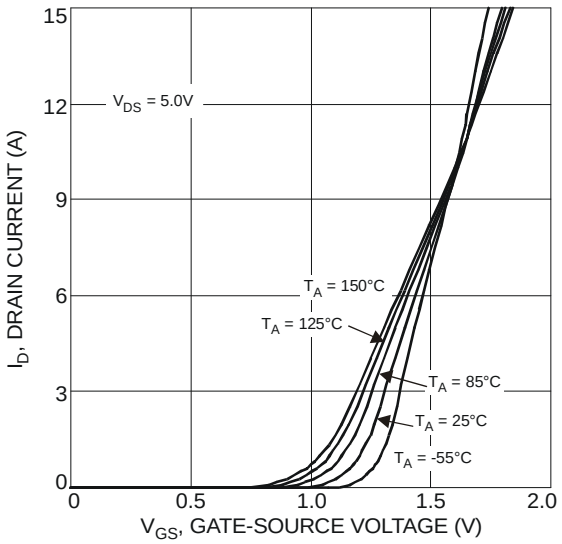

Fig. 2 Typical Transfer Characteristics

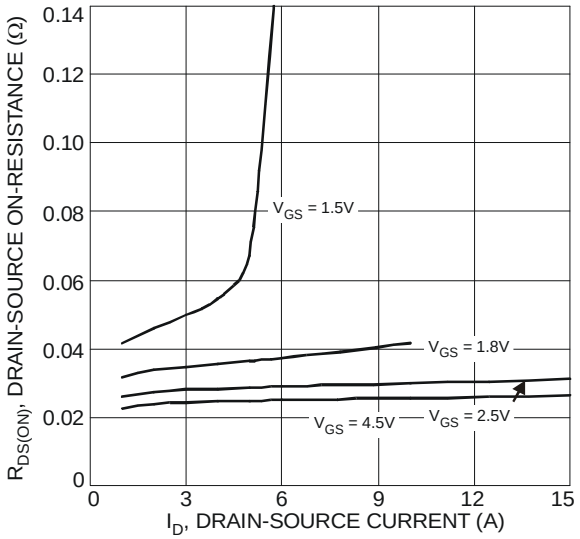

Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

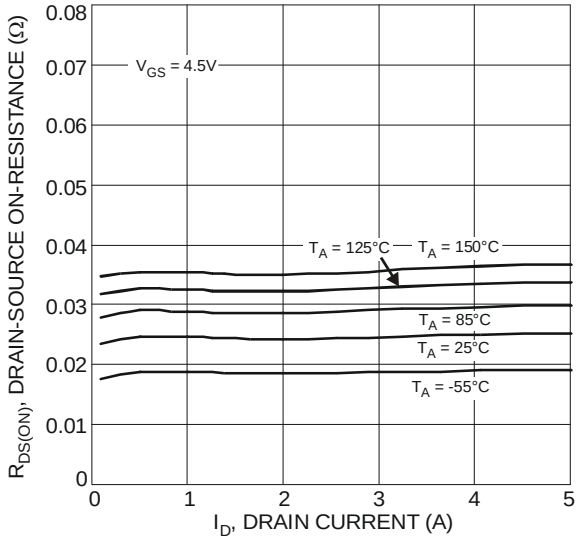

Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

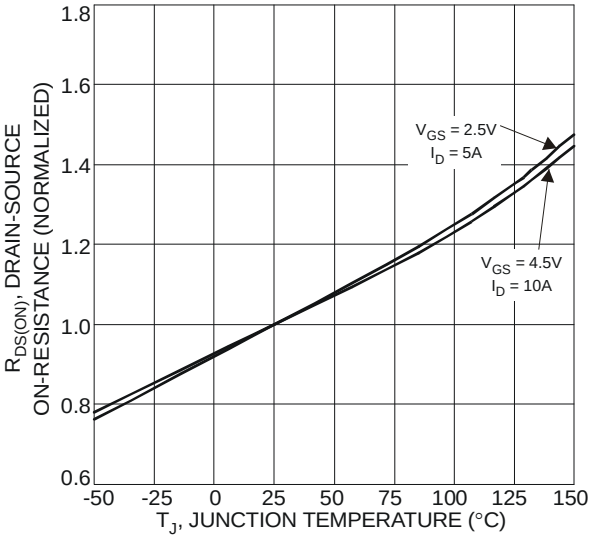

Fig. 5 On-Resistance Variation with Temperature

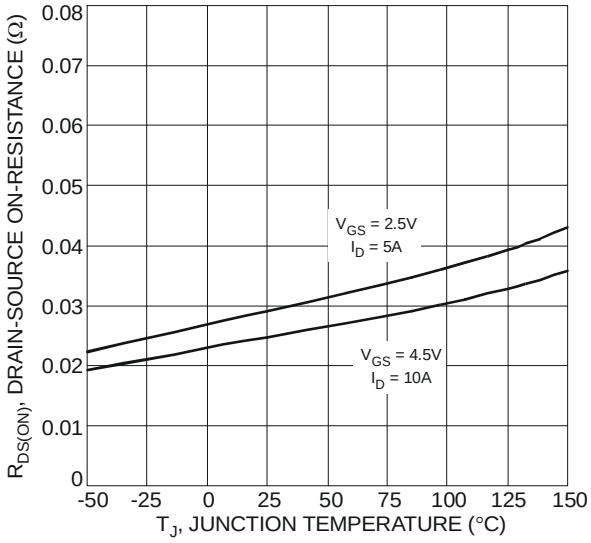

Fig. 6 On-Resistance Variation with Temperature

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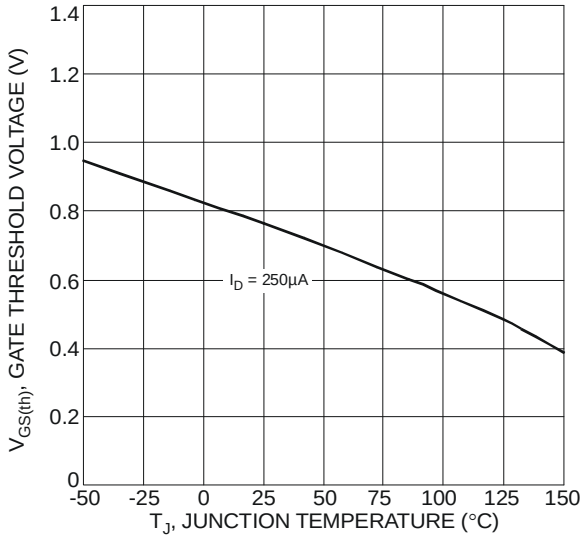

Fig. 7 Gate Threshold Variation vs. Ambient Temperature

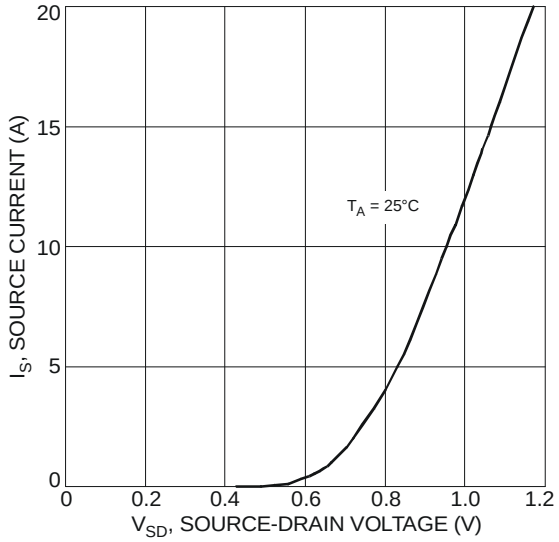

Fig. 8 Diode Forward Voltage vs. Current

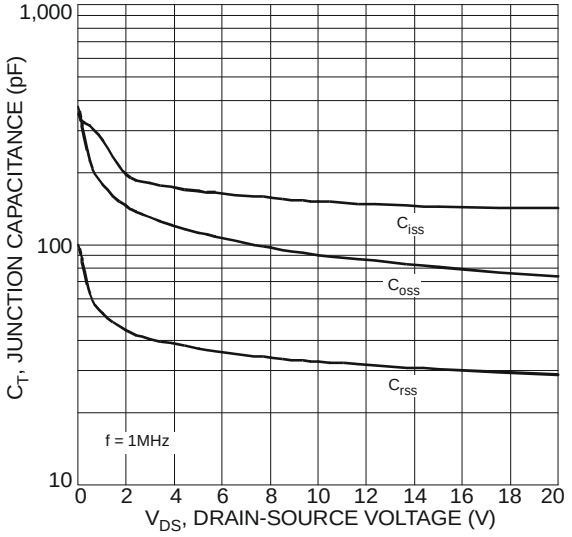

Fig. 9 Typical Junction Capacitance

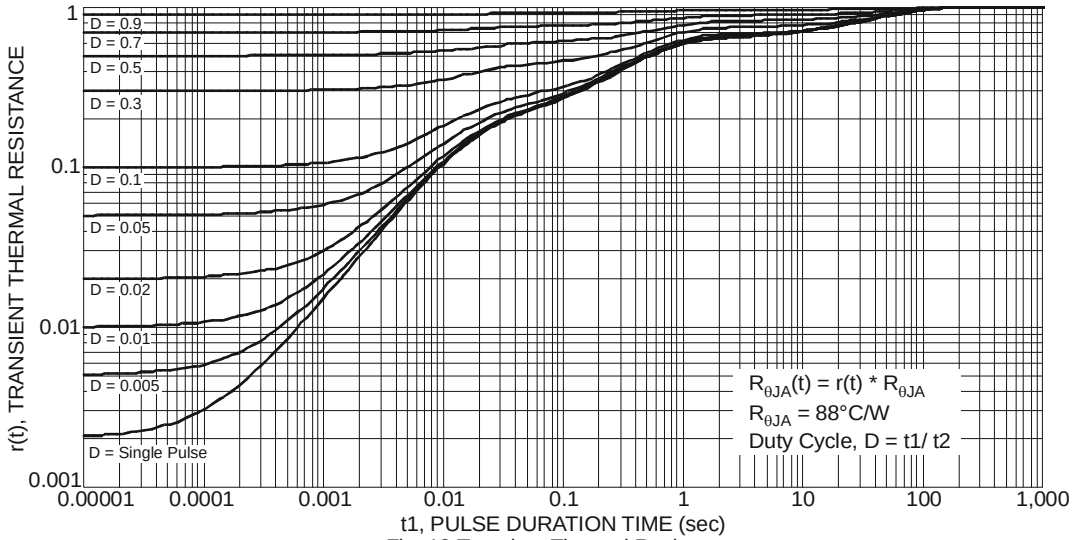

Fig. 10 Transient Thermal Resistance

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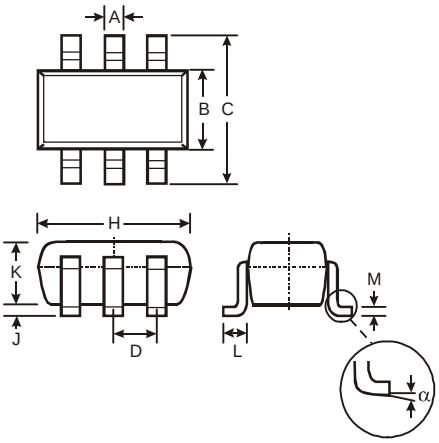
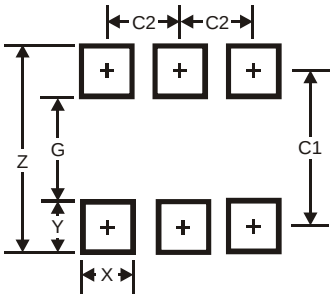
Package Outline Dimensions



SOT26			
Dim	**Min**	**Max**	**Typ**
A	0.35	0.50	0.38
B	1.50	1.70	1.60
C	2.70	3.00	2.80
D	—	—	0.95
H	2.90	3.10	3.00
J	0.013	0.10	0.05
K	1.00	1.30	1.10
L	0.35	0.55	0.40
M	0.10	0.20	0.15
α	0°	8°	—
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.20
G	1.60
X	0.55
Y	0.80
C1	2.40
C2	0.95

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Адрес: 105318, г.Москва, ул.Щербаковская д.3, офис 1107

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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:
moschip.ru
moschip.ru_4
moschip.ru_6
moschip.ru_9